

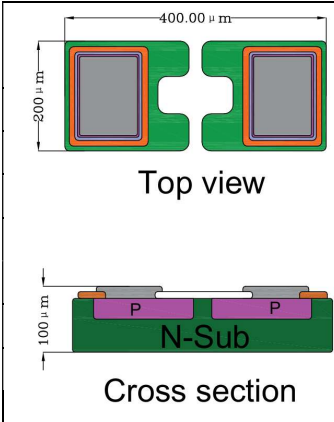
FEATURES

- ◎ Low leakage current
- ◎ Applicable to flip chip Zener package

Structure

- ◎ Lateral PNP Bi-directional Structure
- ◎ Structure: Dual pad

MECHANICAL DATA

 Top view Cross section	Die size($\mu\text{m} \times \mu\text{m}$) (without scribe line)		400.0*200.0
	Die thickness(μm)		100.0
	Scribe line(μm)		40.0
	Bonding pad size(μm^2)	Top	150.0*120.0*2.0
	Top	Metallization	AuSn
		Thickness(μm)	3.0
	Bottom	Metallization	Si
	Wafer size(mm)		$\phi 150$
	Quantity (K pcs)		159

ABSOLUTE MAXIMUM RATINGS (TA=25°C, RH=45%-75%, unless otherwise noted)

Parameter	Symbol	Value	Unit
Operating junction temperature	T _J	150	°C
Storage temperature range	T _{STG}	-55 to +150	°C
Power dissipation	P _d	50	mW

ELECTRICAL CHARACTERISTICS (TA=25°C)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward zener voltage	V _{Z(F)}	I _F =5mA	7	8	10	V
Reverse zener voltage	V _{Z(R)}	I _Z =5mA	7	8	10	V
Forward current	I _F	V _F =4V			0.1	μA
Reverse current	I _R	V _R =4V			0.1	μA

SCHEMATIC&PIN CONFIGURATION

